



- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology



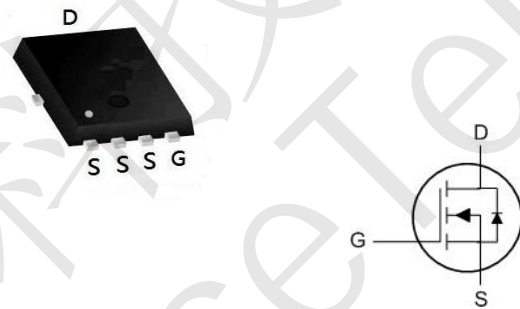
CST80N03F Product Summary

BVDSS	RDSON	ID
30V	3.8mΩ	80A

CST80N03F Description

The CST80N03F is the high cell density Trench MOSFET, which provide excellent RDSON and gate charge for DC/DC converters application. The CST80N03F meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

CST80N03F PDFN5060-8L Pin Configuration



CST80N03F Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	80	A
Drain Current-Continuous(T _c =100°C)	I _D (100°C)	46	A
Pulsed Drain Current ^(Note 1)	I _{DM}	200	A
Maximum Power Dissipation	P _D	65	W
Derating factor		0.52	W/°C
Single pulse avalanche energy ^(Note 5)	E _{AS}	150	mJ
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	1.92	°C/W
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CST80N03F N-Ch 30V Fast Switchin MOSFETs

CST80N03F Electrical Characteristics (TC=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.6	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$	-	3.8	5.0	m Ω
		$V_{GS}=4.5V, I_D=20A$	-	6.9	11.0	
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=20A$	20	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0MHz$	-	1400	-	PF
Output Capacitance	C_{oss}		-	205	-	PF
Reverse Transfer Capacitance	C_{rss}		-	177	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, I_D=20A$ $V_{GS}=10V, R_{GEN}=6\Omega$	-	9	-	nS
Turn-on Rise Time	t_r		-	8	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	28	-	nS
Turn-Off Fall Time	t_f		-	5	-	nS
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=20A,$ $V_{GS}=10V$	-	32.3	-	nC
Gate-Source Charge	Q_{gs}		-	4.9	-	nC
Gate-Drain Charge	Q_{gd}		-	6.9	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=20A$	-	0.85	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	80	A
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ C, I_F = 20A$ $di/dt = 100A/\mu s$ (Note 3)	-	-	27	nS
Reverse Recovery Charge	Q_{rr}		-	-	20	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^\circ C, V_{DD}=15V, V_G=10V, L=0.5mH, R_g=25\Omega$



CST80N03F Typical Electrical and Thermal Characteristics (Curves)

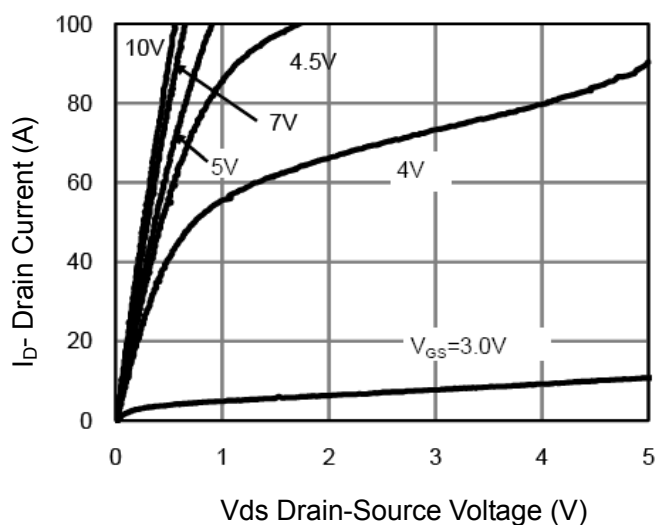


Figure 1 Output Characteristics

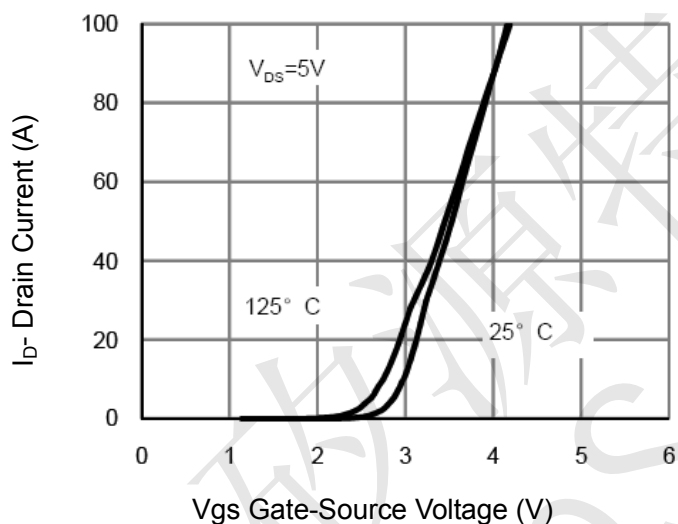


Figure 2 Transfer Characteristics

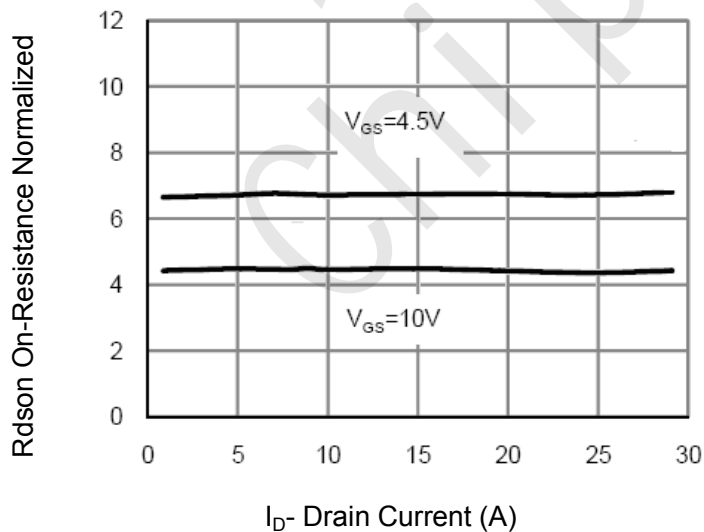


Figure 3 $R_{DS(on)}$ vs Drain Current

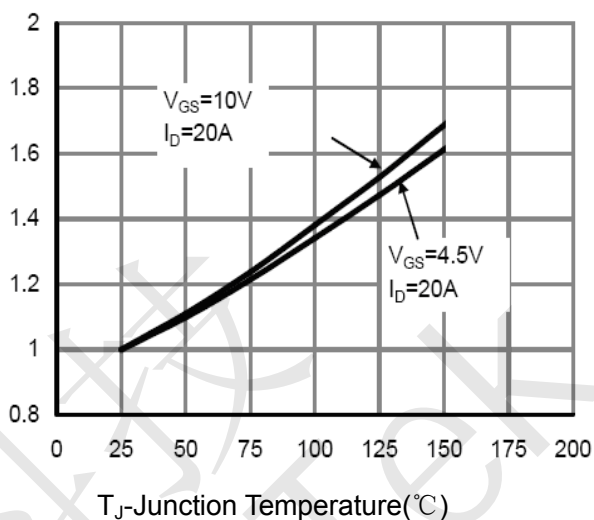


Figure 4 $R_{DS(on)}$ vs Junction Temperature

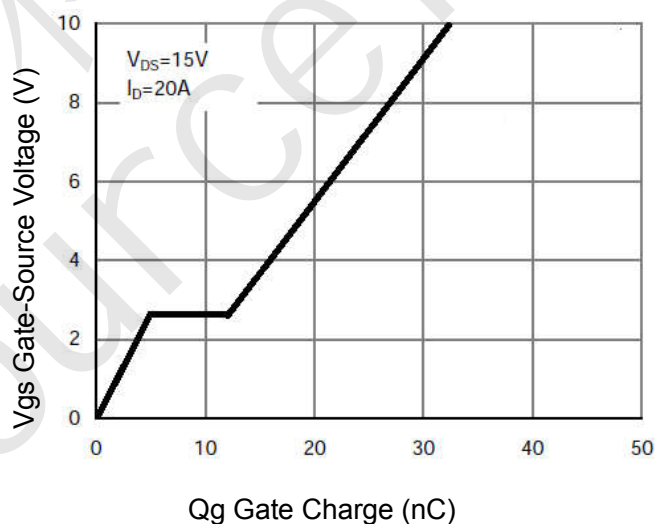


Figure 5 Gate Charge

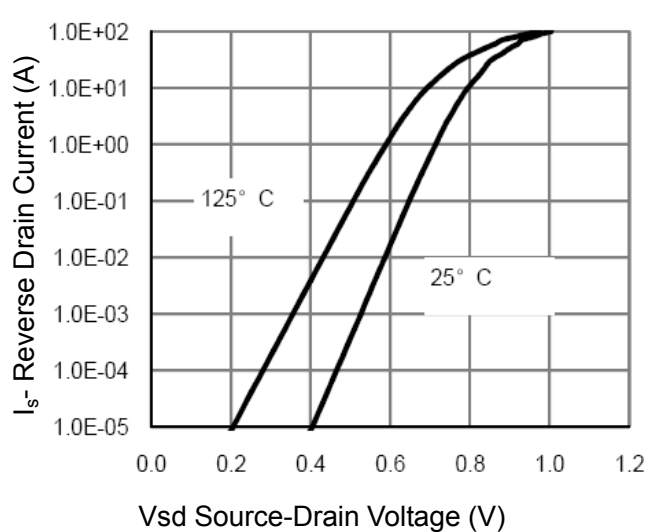
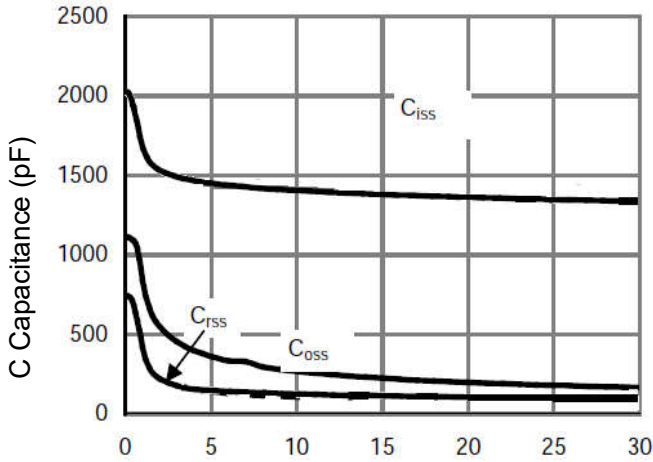
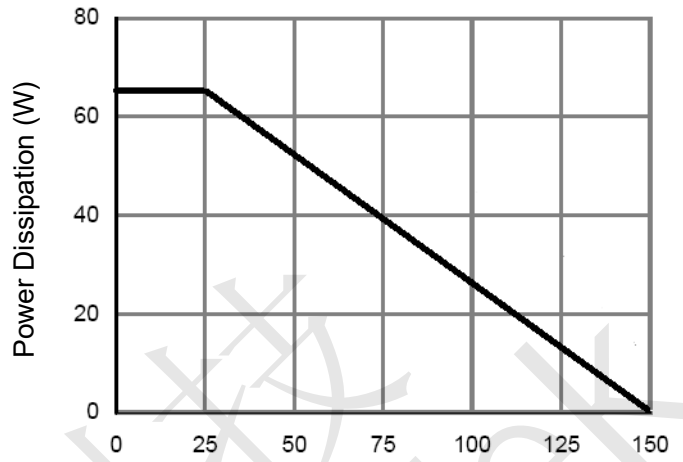


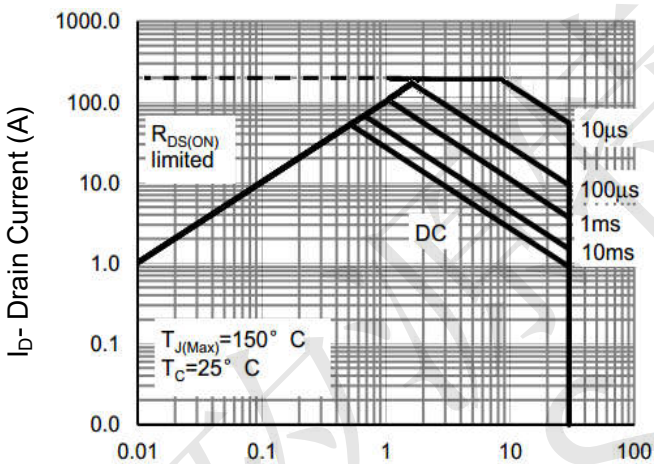
Figure 6 Source-Drain Diode Forward



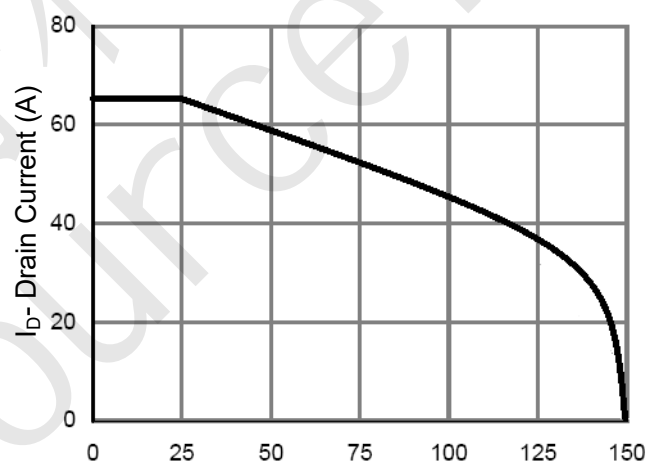
Vds Drain-Source Voltage (V)
Figure 7 Capacitance vs Vds



T_J-Junction Temperature(°C)
Figure 9 Power De-rating



Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area



T_J-Junction Temperature(°C)
Figure 10 ID Current- Junction Temperature

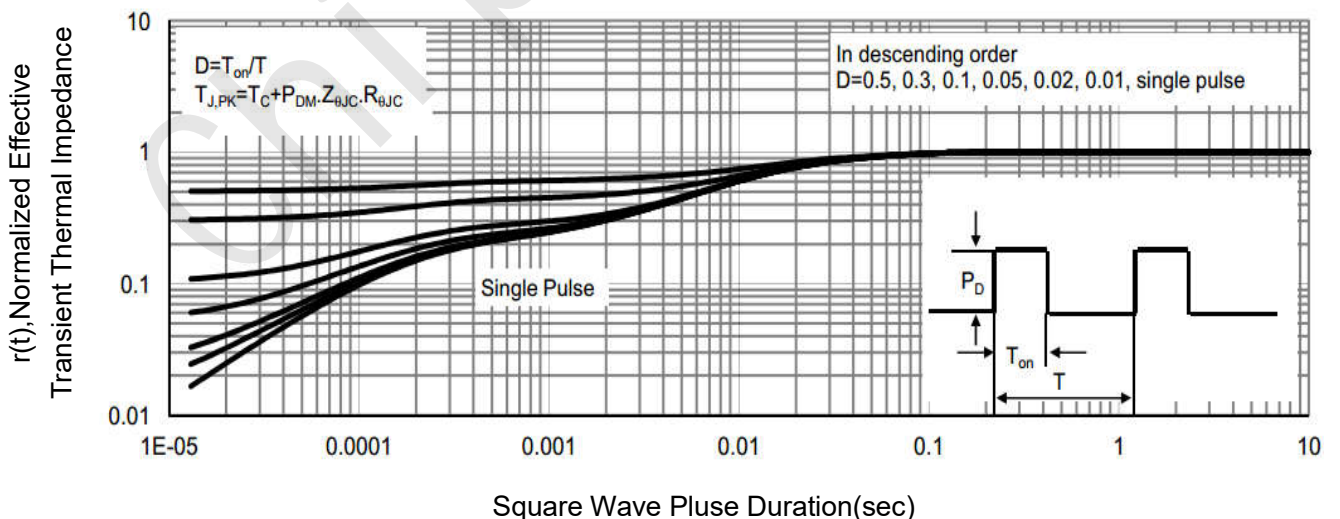


Figure 11 Normalized Maximum Transient Thermal Impedance



CST80N03F Test Circuit

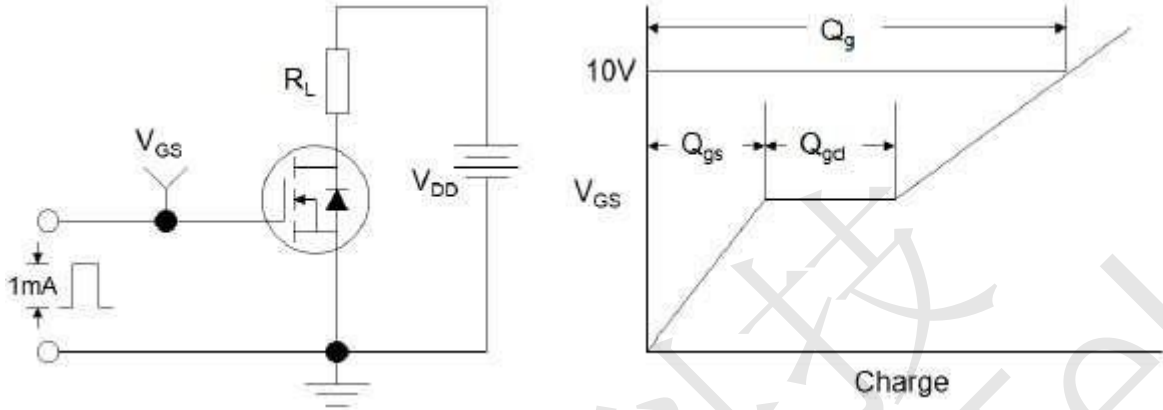


Figure1:Gate Charge Test Circuit & Waveform

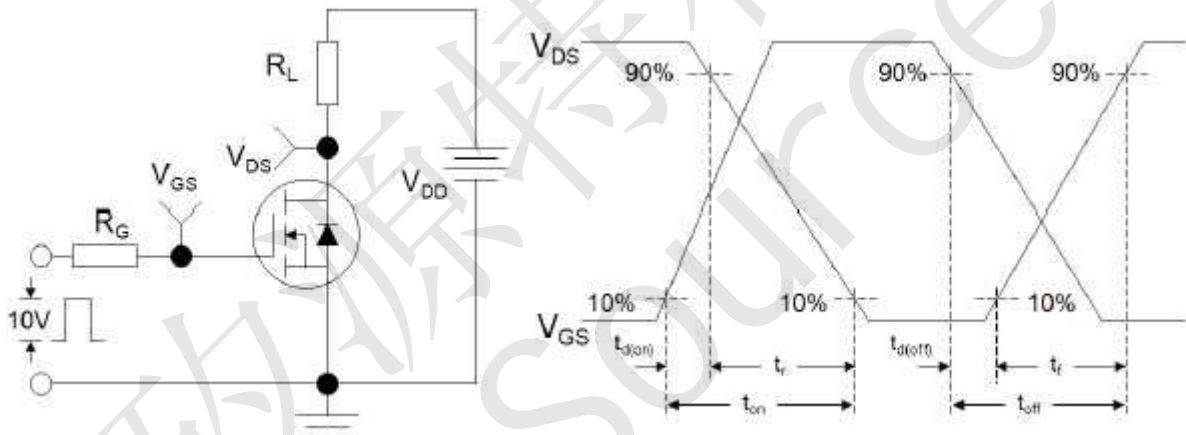


Figure 2: Resistive Switching Test Circuit & Waveforms

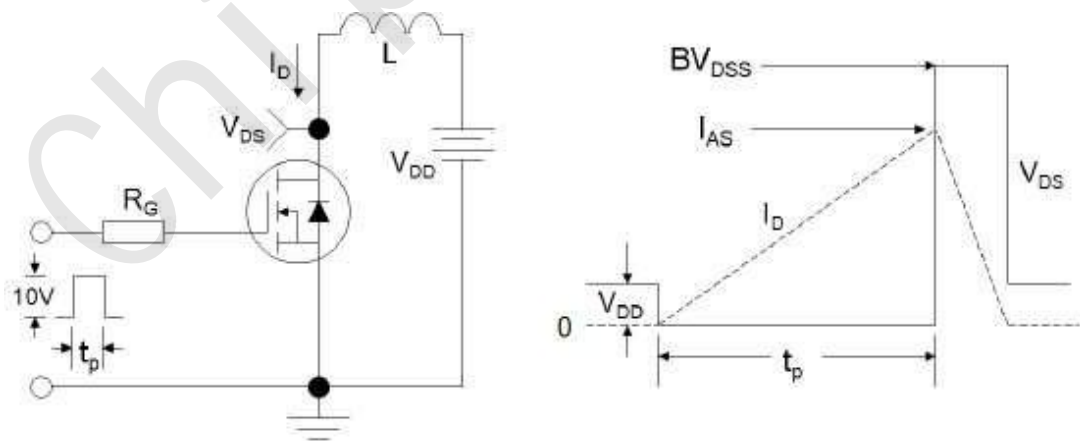
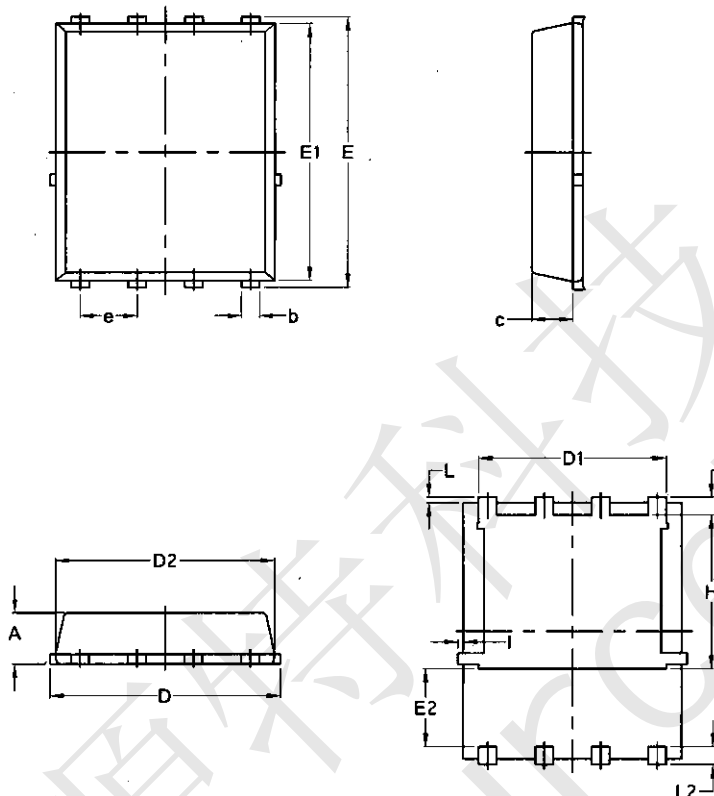


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms



CST80N03F Package Mechanical Data-PDFN5060-8L-JQ Single



Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070